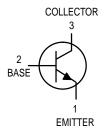
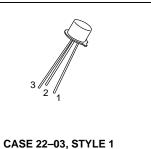
High Voltage Transistors NPN Silicon



BSS71



TO-18 (TO-206AA)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	200	Vdc
Collector-Base Voltage	V _{CBO}	200	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current — Continuous	IC	0.5	Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	0.5 2.86	Watts mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	2.5 14.3	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta}$ JC	70	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit		
OFF CHARACTERISTICS							
Collector-Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0) ⁽¹⁾	V(BR)CEO	200	_	_	Vdc		
Collector – Base Breakdown Voltage ($I_C = 100 \mu Adc$, $I_E = 0$)	V(BR)CBO	200	_	_	Vdc		
Emitter-Base Breakdown Voltage ($I_E = 100 \mu Adc$, $I_C = 0$)	V(BR)EBO	6.0	_	_	Vdc		
Collector Cutoff Current (V _{CB} = 150 Vdc, I _E = 0)	ICBO	_	_	50	nAdc		
Collector-Emitter Cutoff Current (V _{CE} = 150 Vdc, I _B = 0)	ICEO	_	_	500	nAdc		
Emitter Cutoff Current (V _{EB} = 5.0 Vdc, I _C = 0)	I _{EBO}	_	_	50	nAdc		
ON CHARACTERISTICS							

DC Current Gain (I _C = 0.1 mAdc, V _{CE} = 1.0 Vdc) (I _C = 1.0 mAdc, V _{CE} = 10 Vdc) (I _C = 10 mAdc, V _{CE} = 10 Vdc) (I _C = 30 mAdc, V _{CE} = 10 Vdc)(1)	hFE	20 30 50 40	40 45 120 140	— — — 250	_
Collector–Emitter Saturation Voltage(1) (I _C = 10 mAdc, I _B = 1.0 mAdc) (I _C = 30 mAdc, I _B = 3.0 mAdc) (I _C = 50 mAdc, I _B = 5.0 mAdc)	VCE(sat)	_ _ _ _	0.15 0.25 0.35	0.3 0.4 0.5	Vdc
Base–Emitter Saturation Voltage ⁽¹⁾ $(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc})$ $(I_C = 30 \text{ mAdc}, I_B = 3.0 \text{ mAdc})$ $(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$	VBE(sat)	111	0.7 0.8 0.85	0.8 0.9 1.0	Vdc

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Tun	Max	Unit	
Characteristic	Symbol	IVIII	Тур	IVIAX	Unit	
DYNAMIC CHARACTERISTICS	DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product ($I_C = 20 \text{ mAdc}$, $V_{CE} = 20 \text{ Vdc}$, $f = 20 \text{ MHz}$)	f _t	50	70	200	MHz	
Output Capacitance (I _E = 0, V _{CB} = 20 Vdc, f = 1.0 MHz)	C _{ob}	_	3.5	_	pF	
Input Capacitance (I _C = 0, V_{EB} = 0.5 Vdc, f = 1.0 MHz)	C _{ib}	_	45	_	pF	
Turn–On Time ($I_{B1} = 10 \text{ mAdc}$, $I_{C} = 50 \text{ mAdc}$, $V_{CC} = 100 \text{ Vdc}$)	ton	_	100	_	ns	
Turn–Off Time ($I_{B2} = 10 \text{ mAdc}$, $I_{C} = 50 \text{ mAdc}$, $V_{CC} = 100 \text{ Vdc}$)	toff	_	400	_	ns	

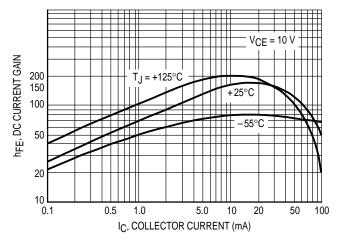


Figure 1. DC Current Gain

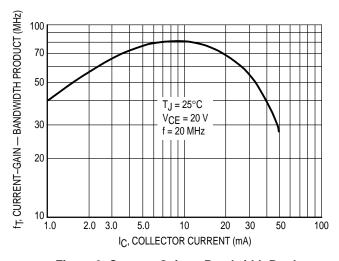


Figure 3. Current-Gain — Bandwidth Product

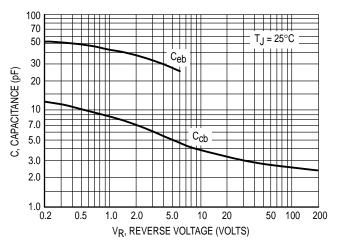


Figure 2. Capacitances

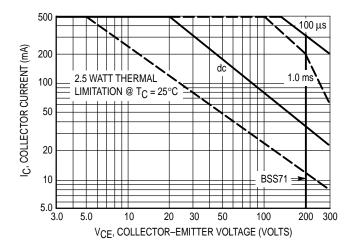


Figure 4. Active-Region Safe Operating Area

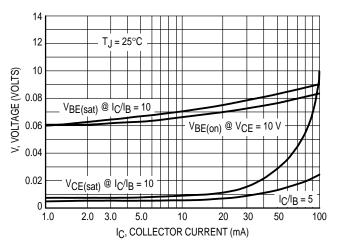


Figure 5. "On" Voltages

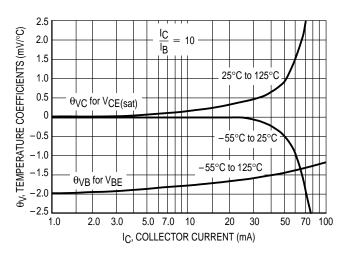


Figure 6. Temperature Coefficients

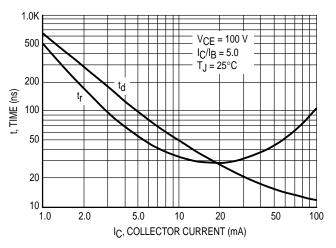


Figure 7. Turn-On Time

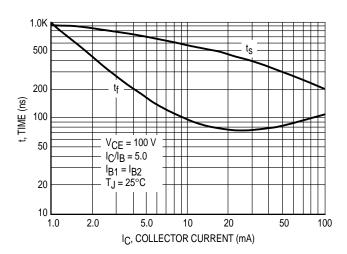


Figure 8. Turn-Off Time

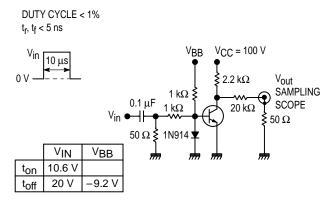
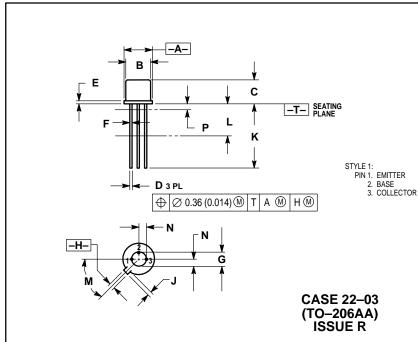


Figure 9. Switching Time Test Circuit

PACKAGE DIMENSIONS



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 DIMENSION J MEASURED FROM DIMENSION A MAXIMUM.
- DIMENSION F APPLIES BETWEEN DIMENSION P AND L. DIMENSION D APPLIES BETWEEN DIMENSION L AND K MINIMUM, LEAD DIAMETER IS UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.
- DIMENSION E INCLUDES THE TAB THICKNESS. (TAB THICKNESS IS 0.51(0.002) MAXIMUM).

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN MAX		
Α	0.209	0.230	5.31	5.84	
В	0.178	0.195	4.52	4.95	
O	0.170	0.210	4.32	5.33	
D	0.016	0.021	0.406	0.533	
Е		0.030		0.762	
F	0.016	0.019	0.406	0.483	
Ð	0.100	BSC	2.54 BSC		
Η	0.036	0.046	0.914	1.17	
۲	0.028	0.048	0.711	1.22	
K	0.500		12.70		
٦	0.250		6.35		
M	45 °BSC		45°BSC		
N	0.050	BSC	1.27 BSC		
Р		0.050		1.27	

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